L Number	Hits	Search Text	DB	Time stamp
1	2	(("5699375") or ("5963568")).PN.	USPAT	2003/03/07 13:38
2	2		USPAT;	2003/03/07 13:38
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	2003/03/07 13:38
			EPO; JPO;	
			DERWENT;	
-	0	(plurality near2 semiconductor near2 resonat\$4) and	IBM_TDB	0000100107.15.55
		372/\$ and group adj V	USPAT;	2003/03/07 13:36
		372/4 and group auj V	US-PGPUB;	
			EPO; JPO;	
1]		DERWENT;	
1_	3	/alivality	IBM_TDB	
	3	(plurality near semiconductor near resonat\$5) and	USPAT;	2002/03/18 16:03
		372/\$	US-PGPUB;	
			EPO; JPO;	'
			DERWENT;	
	70.		IBM_TDB	
-	734	(semiconductor near3 resonat\$5) and 372/\$	USPAT;	2002/09/09 09:17
	0 •		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	15	(semiconductor near2 resonat\$4) and 372/\$ and	USPAT;	2002/03/18 16:05
		group adj V	US-PGPUB:	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	222	((semiconductor near3 resonat\$5) and 372/\$) and	USPAT;	2002/03/18 16:39
		((high near resistance) or groove)	US-PGPUB;	2002/00/10 10:55
		·	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	11	(((semiconductor near3 resonat\$5) and 372/\$) and	USPAT;	2002/03/18 16:07
		((high near resistance) or groove)) and	US-PGPUB;	2002/03/10 10.07
		((semiconductor near2 resonat\$4) and 372/\$ and	EPO; JPO;	
		group adj V)	DERWENT;	
			IBM TDB	
-	35	((semiconductor near3 resonat\$5) and 372/\$) and	USPAT;	2002/03/18 16:40
		((high near resistance) and groove)	US-PGPUB;	2002/03/16 10:40
	i		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	70	((semiconductor near3 resonat\$5) and 372/\$) and	USPAT;	2002/02/19 16:40
		((high near resistance) or (stripe near shaped near	US-PGPUB;	2002/03/18 16:40
[groove))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3	((semiconductor near3 resonat\$5) and 372/\$) and	-	2002/02/10 17:01
[-	((high near resistance) and (stripe near shaped near	USPAT;	2002/03/18 17:01
	ľ	groove))	US-PGPUB;	
		₩ ₩II	EPO; JPO;	
			DERWENT;	
-	1	(((semiconductor near3 resonat\$5) and 372/\$) and	IBM_TDB	0000/00/10
	. 1	((high near resistance) and (stripe near shaped near	USPAT;	2002/03/18 16:44
		groove))) and group adj V	US-PGPUB;	1
Ì	ĺ	a. a	EPO; JPO;	
	i		DERWENT;	
			IBM_TDB	

	7	/ ///somiconductor noor2 recondet5) and 270/6)	T. 10-1-	
	′	(((semiconductor near3 resonat\$5) and 372/\$) and ((high near resistance) and groove)) and group adj V	1	2002/03/18 16:4
		triigii fical resistance, and groove), and group ad, v	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	11	The state of the s	USPAT;	2002/03/19 09:5
		((high near resistance) or (stripe near shaped near	US-PGPUB;	
		groove))) and group adj V	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	4	((semiconductor near3 resonat\$5) and 372/\$) and	USPAT;	2002/03/18 17:0
	ĺ	((high near resistance) and (stripe near groove))	US-PGPUB;	2002/03/16 17:0
		the second control of the feet groover		
		*	EPO; JPO;	
			DERWENT;	
_	28	(//comission dupter and 2 may 145)	IBM_TDB	
	20	The state indicate indicated and 372/4 failu	USPAT;	2002/03/19 09:0
		(((high and low) near resistance) or (stripe near	US-PGPUB;	
		shaped near groove)))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(((semiconductor near3 resonat\$5) and 372/\$) and	USPAT;	2002/03/19 09:0
		(((high and low) near resistance) and (stripe near	US-PGPUB;	2002/03/13 03.0
		shaped near groove)))	EPO; JPO;	
	i	J	DERWENT;	
-	70	(((semiconductor near3 resonat\$5) and 372/\$) and	IBM_TDB	
	,0	((bigh poor resistance) (high poor resistance)	USPAT;	2002/03/19 09:0:
		((high near resistance) or (stripe near shaped near	US-PGPUB;	
		groove)))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 09:03
		(high near resistance) and (low near resistance) and	US-PGPUB;	
		(stripe near shaped near groove)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	17	(semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 09:03
	1	(stripe near shaped near groove)	US-PGPUB;	2002/03/19 09:03
		ground ground		
			EPO; JPO;	
			DERWENT;	
	24	(somiconductor poor? reserve (AE)	IBM_TDB	
	24	(semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 09:03
		(stripe near groove)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	201	(semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 09:03
		(groove)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	29	(semiconductor near3 resonat\$5) and 372/\$ and	IBM_TDB	
	[23	(groove) and (register \$5 are 1)	USPAT;	2002/03/19 09:20
		(groove) and (resistan\$5 near (region or layer or film	US-PGPUB;	
	1	or medium))	EPO; JPO;	
		İ	DERWENT;	
]		IBM TDB	
	29	(semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 09:22
]	(groove or (stripe near groove) or (shaped near	US-PGPUB;	-002/03/13 03.22
		groove)) and (resistan\$5 near (region or layer or film		
		or medium))	EPO; JPO;	
			DERWENT; IBM TDB	

	1 45			
-	15	me and the state of the state o	USPAT;	2002/03/19 09:56
		(groove or (stripe near groove) or (shaped near	US-PGPUB;	
		groove)) and (resistan\$5 near (region or layer or film	EPO; JPO;	
		or medium))) and (group near V)	DERWENT;	
1		Westign 1 in 10	IBM_TDB	
-	4	The strategic fied of tesonates and 372/5 and	USPAT;	2002/03/19 10:19
		(groove or (stripe near groove) or (shaped near	US-PGPUB;	
1		groove)) and (resistan\$5 near (region or layer or film	EPO; JPO;	
		or medium))) and (group near V)) and infrared	DERWENT;	
			IBM_TDB	
1	3	Title of the detect fled of tesofiates and 372/4 and	USPAT;	2002/03/19 09:59
		(groove or (stripe near groove) or (shaped near	US-PGPUB;	-
1		groove)) and (resistan\$5 near (region or layer or film	EPO; JPO;	
	1	or medium))) and (group near V)) and infrared) and	DERWENT;	
		(refractive near (index or indice or indec))	IBM_TDB	
] -	0	Mesimostication readilates/ and 372/4 and	USPAT;	2002/03/19 10:01
		(groove or (stripe near groove) or (shaped near	US-PGPUB;	
		groove)) and (resistan\$5 near (region or layer or film	EPO; JPO;	
		or medium))) and (air near gap)	DERWENT;	
			IBM_TDB	
-	3	((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 10:19
		(groove)) and (air near gap)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	78	((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/08/26 10:57
		(groove)) and (insulat\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4	((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 10:12
		(groove)) and (electrical\$4 near insulat\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 10:12
		(groove)) and (groove near insulat\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	((((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 10:20
1		(groove)) and (groove near insulat\$4)) and infrared)	US-PGPUB;	
		and (air near gap)	EPO; JPO;	
İ			DERWENT;	
_		Wasania at a sama a	IBM_TDB	
-	1 1	(((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 12:44
]	(groove)) and (groove near insulat\$4)) and infrared	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
_		Hannahan I	IBM_TDB	
=		((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/19 12:44
		(groove)) and dc and dvd	US-PGPUB;	
			EPO; JPO;	
		ı	DERWENT;	
_		Hanning day	IBM_TDB	
-		((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/03/21 16:56
		(groove)) and (insulat\$4) and (cd or dvd)	US-PGPUB;	
			EPO; JPO;	
		İ	DERWENT;	
			IBM_TDB	

-	0	Keeming to the transfer of the content of the conte	USPAT;	2002/03/21 16:57
İ		(groove)) and (insulat\$4) and (cd AND dvd)	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	484	(VCSEL or (vertical near cavity near surface near	USPAT;	2002/08/26 11:06
		emit\$5 near laser) or (semiconductor near laser))	US-PGPUB;	2002/00/20 11:00
		same (material near3 different)	EPO; JPO;	
			DERWENT;	
_	245	(VCSEL or (vertical near cavity near surface near	IBM_TDB	000000000000000
	243	emit\$5 near laser) or (semiconductor near laser))	USPAT;	2002/08/26 11:07
		WITH (material near3 different)	US-PGPUB;	-
		with (material nears different)	EPO; JPO;	
			DERWENT;	
		10.00	IBM_TDB	-
i -	213	((VCSEL or (vertical near cavity near surface near	USPAT;	2002/08/26 11:07
		emit\$5 near laser) or (semiconductor near laser))	US-PGPUB;	
		same (material near3 different)) and (Gallium or	EPO; JPO;	
		photons)	DERWENT;	
			IBM TDB	
-	29	((VCSEL or (vertical near cavity near surface near	USPAT;	2002/08/26 11:07
		emit\$5 near laser) or (semiconductor near laser))	US-PGPUB;	
		same (material near3 different)) and (Gallium or	EPO; JPO;	
	İ	photons) and red and infrared	DERWENT;	
1			IBM TDB	
-	105	((VCSEL or (vertical near cavity near surface near	USPAT;	2002/08/26 11:07
		emit\$5 near laser) or (semiconductor near laser))	US-PGPUB;	2002/08/28 11:07
		WITH (material near3 different)) and (Gallium or		
		photons)	EPO; JPO;	
		photonay	DERWENT;	
_	19	//VCSEL or /vorticel near again, and a	IBM_TDB	
	13	((VCSEL or (vertical near cavity near surface near	USPAT;	2002/08/26 11:24
		emit\$5 near laser) or (semiconductor near laser))	US-PGPUB;	
		WITH (material near3 different)) and (Gallium or	EPO; JPO;	
		photons) and red and infrared	DERWENT;	
	_	10.1005	IBM_TDB	
_	7	((VCSEL or (vertical near cavity near surface near	USPAT;	2002/08/26 11:25
		emit\$5 near laser) or (semiconductor near laser))	US-PGPUB;	
		WITH (material near3 different)) and ((Gallium near	EPO; JPO;	
		ion) or photons) and red and infrared	DERWENT;	
			IBM_TDB	
-	60	(semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/09/09 09:26
		((different or (non adj similar) or dissimilar or other or	US-PGPUB;	
		ohterwose or unalike or unlike or unequal or	EPO; JPO;	
		unsimilar or various) near material)	DERWENT;	
		·	IBM TDB	
-	0	((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/09/09 09:29
		((different or (non adj similar) or dissimilar or other or	US-PGPUB;	
		ohterwose or unalike or unlike or unequal or	EPO; JPO;	
		unsimilar or various) near material)) and (red and	DERWENT;	
		infrared) and (protons or gallium) and (air near2 gap)	IBM_TDB	
-	4	((semiconductor near3 resonat\$5) and 372/\$ and	USPAT;	2002/09/09 09:48
		((different or (non adj similar) or dissimilar or other or	US-PGPUB;	2002103103 03:48
		ohterwose or unalike or unlike or unequal or	EPO; JPO;	
		unsimilar or various) near material)) and (red and	DERWENT;	
		infrared) and (protons or gallium)		
-	4	(((semiconductor near3 resonat\$5) and 372/\$ and	IBM_TDB	2000/00/00 55 55
		((different or (non adj similar) or dissimilar or other or	USPAT;	2002/09/09 09:48
		ohterwose or unalike or unlike or unequal or	US-PGPUB;	
		uncimilar or various) poor metaricily and the	EPO; JPO;	
		unsimilar or various) near material)) and (red and	DERWENT;	
		infrared) and (protons or gallium)) and substrate	IBM_TDB	

	7216	((plurality or more or multi\$4 or two) near laser) and	USPAT;	2003/03/07 11:03
		active	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	62	((plurality ro multi\$4 or more or two) near2	USPAT;	2003/03/07 11:07
!		semiconductor near2 resonat\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	796	((plurality or more or multi\$4 or two) near laser near	USPAT;	2003/03/07 11:06
		semiconductor) and active	US-PGPUB;	•
			EPO; JPO;	
		5	DERWENT;	
			IBM_TDB	•
-	26	(((plurality ro multi\$4 or more or two) near2	USPAT;	2003/03/07 11:07
		semiconductor near2 resonat\$4)) and active and	US-PGPUB;	
		substrate	EPO; JPO;	
			DERWENT;	
			IBM TDB	